

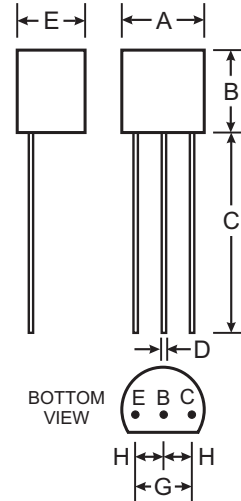
## NPN EPITAXIAL PLANAR TRANSISTOR

### Features

- Suitable for AF Driver and Low Power Output Stage Applications
- Available in Sub-Groups Graded by DC Current Gain
- 625mW Power Dissipation

### Mechanical Data

- Case: TO-92, Plastic
- Leads: Solderable per MIL-STD-202, Method 208
- Pin Connections: See Diagram
- Weight: 0.18 grams (approx.)



TO-92		
Dim	Min	Max
A	4.45	4.70
B	4.46	4.70
C	12.7	—
D	0.41	0.63
E	3.43	3.68
G	2.42	2.67
H	1.14	1.40
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector Emitter Voltage	$V_{CEO}$	45	V
Emitter Base Voltage	$V_{EBO}$	5.0	V
Collector Current	$I_C$	800	mA
Peak Collector Current	$I_{CM}$	1.0	A
Base Current	$I_B$	100	mA
Power Dissipation (Note 1)	$P_d$	625	mW
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics $25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
DC Current Gain	Current Gain Group 16	100	160	250	—	$V_{CE} = 1.0\text{V}, I_C = 100\text{mA}$
		25	160	250		
		40	250	400		
	Current Gain Group 16	250	400	630		$V_{CE} = 1.0\text{V}, I_C = 300\text{mA}$
		60	130	—		
		100	200	—		
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	—	—	200	K/W	Note 1
Collector-Emitter Cutoff Current	$I_{CES}$	—	2.0	100	nA	$V_{CE} = 45\text{V}$
			—	10	$\mu\text{A}$	$V_{CE} = 45\text{V}, T_A = 125^\circ\text{C}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}$
	$V_{(BR)CES}$	50	—	—	V	$I_C = 0.1\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5.0	—	—	V	$I_E = 0.1\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	0.7	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Voltage	$V_{BE}$	—	—	1.2	V	$V_{CE} = 1.0\text{V}, I_C = 300\text{mA}$
Gain Bandwidth Product	$f_T$	—	100	—	MHz	$V_{CE} = 5\text{V}, I_C = 10\text{mA}, f = 50\text{MHz}$
Collector-Base Capacitance	$C_{CBO}$	—	12	—	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$

Notes: 1. Valid provided that leads are kept at ambient temperature at a distance of 2.0mm from case.

